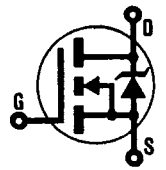


INTERNATIONAL RECTIFIER **IR**

REPETITIVE AVALANCHE AND dv/dt RATED*
 LOWER ON STATE RESISTANCE, 175°C OPERATING TEMPERATURE

HEXFET® TRANSISTORS

- IRF530**
- IRF531**
- IRF532**
- IRF533**



N-CHANNEL

100 Volt, 0.16 Ohm HEXFET TO-220AB Plastic Package

The HEXFET® technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of this latest "State of the Art" design achieves: very low on-state resistance combined with high transconductance; superior reverse energy and diode recovery dv/dt capability.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, very fast switching, ease of paralleling and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers and high energy pulse circuits.

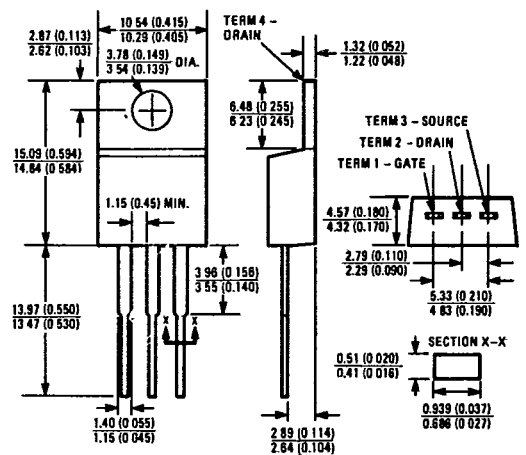
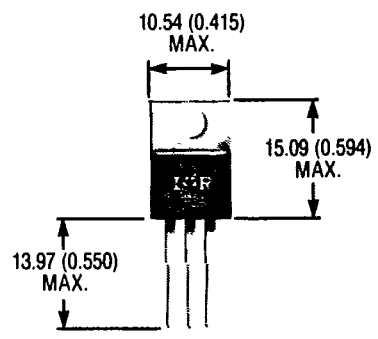
Product Summary

Part Number	V _{DS}	R _{DS(on)}	I _D
IRF530	100V	0.16Ω	14A
IRF531	80V	0.16Ω	14A
IRF532	100V	0.23Ω	12A
IRF533	80V	0.23Ω	12A

FEATURES:

- Repetitive Avalanche Ratings
- Dynamic dv/dt Rating
- Simple Drive Requirements
- Ease of Paralleling

CASE STYLE AND DIMENSIONS



Case Style TO-220AB
 Dimensions in Millimeters and (Inches)



*This data sheet applies to product with batch codes that begin with a digit, i.e. 2A3B
 C-199

IRF530, IRF531, IRF532, IRF533 Devices

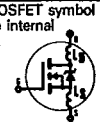
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Absolute Maximum Ratings

Parameter	IRF530, IRF531	IRF532, IRF533	Units
$I_D @ T_C = 25^\circ\text{C}$ Continuous Drain Current	14	12	A
$I_D @ T_C = 100^\circ\text{C}$ Continuous Drain Current	10	8.3	A
I_{DM} Pulsed Drain Current ①	56	48	A
$P_D @ T_C = 25^\circ\text{C}$ Max. Power Dissipation	79		W
Linear Derating Factor	0.53		W/K ②
V_{GS} Gate-to-Source Voltage	± 20		V
E_{AS} Single Pulse Avalanche Energy ②	69 (See Fig. 14)		mJ
I_{AR} Avalanche Current ③ (Repetitive or Non-Repetitive)	14 (See E_{AR})		A
E_{AR} Repetitive Avalanche Energy ③	7.9 (See I_{AR})		mJ
dv/dt Peak Diode Recovery dv/dt ④	5.5 (See Fig. 17)		V/ns
T_J Operating Junction Temperature Range	-55 to 175		$^\circ\text{C}$
T_{STG} Storage Temperature Range			$^\circ\text{C}$
Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)		$^\circ\text{C}$

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (Unless Otherwise Specified)

Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS} Drain-to-Source Breakdown Voltage	IRF530 IRF532	100	—	—	V	$V_{GS} = 0V, I_D = 250 \mu\text{A}$
	IRF531 IRF533	80	—	—	V	
$R_{DS(on)}$ Static Drain-to-Source On-State Resistance ④	IRF530 IRF531	—	0.12	0.16	Ω	$V_{GS} = 10V, I_D = 8.3A$
	IRF532 IRF533	—	0.16	0.23	Ω	
$I_{D(on)}$ On-State Drain Current ④	IRF530 IRF531	14	—	—	A	$V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max. $V_{GS} = 10V$
	IRF532 IRF533	12	—	—	A	
$V_{GS(th)}$ Gate Threshold Voltage	ALL	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$
g_{fs} Forward Transconductance ④	ALL	5.1	7.6	—	S (①)	$V_{DS} \geq 50V, I_{DS} = 8.3A$
I_{DSS} Zero Gate Voltage Drain Current	ALL	—	—	250	μA	$V_{DS} = \text{Max. Rating}, V_{GS} = 0V$ $V_{DS} = 0.8 \times \text{Max. Rating}$ $V_{GS} = 0V, T_J = 150^\circ\text{C}$
		—	—	1000		
I_{GSS} Gate-to-Source Leakage Forward	ALL	—	—	500	nA	$V_{GS} = 20V$
I_{GSS} Gate-to-Source Leakage Reverse	ALL	—	—	-500	nA	$V_{GS} = -20V$
Q_g Total Gate Charge	ALL	—	17	28	nC	$V_{GS} = 10V, I_D = 14A$ $V_{DS} = 0.8 \times \text{Max. Rating}$ See Fig. 16
Q_{gs} Gate-to-Source Charge	ALL	—	3.7	5.5	nC	(Independent of operating temperature)
Q_{gd} Gate-to-Drain ("Miller") Charge	ALL	—	7.0	11	nC	(Independent of operating temperature)
$t_{d(on)}$ Turn-On Delay Time	ALL	—	10	15	ns	$V_{DD} = 50V, I_D = 14A, R_G = 12\Omega$
t_r Rise Time	ALL	—	34	51	ns	$R_D = 3.6\Omega$
$t_{d(off)}$ Turn-Off Delay Time	ALL	—	23	35	ns	See Fig. 15
t_f Fall Time	ALL	—	24	38	ns	(Independent of operating temperature)
L_D Internal Drain Inductance	ALL	—	4.5	—	nH	Measured from the drain lead, 6mm (0.25 in.) from package to center of die.
L_S Internal Source Inductance	ALL	—	7.5	—	nH	Measured from the source lead, 6mm (0.25 in.) from package to source bonding pad.
C_{iss} Input Capacitance	ALL	—	650	—	pF	Modified MOSFET symbol showing the internal inductances. 
C_{oss} Output Capacitance	ALL	—	240	—	pF	
C_{rss} Reverse Transfer Capacitance	ALL	—	44	—	pF	

Source-Drain Diode Ratings and Characteristics

Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
I_S Continuous Source Current (Body Diode)	ALL	—	—	14	A	Modified MOSFET symbol showing the integral Reverse p-n junction rectifier. 
I_{SM} Pulsed Source Current (Body Diode) ①	ALL	—	—	56	A	
V_{SD} Diode Forward Voltage ②	ALL	—	—	2.5	V	$T_J = 25^\circ\text{C}$, $I_S = 14\text{A}$, $V_{GS} = 0\text{V}$
t_{rr} Reverse Recovery Time	ALL	55	120	250	ns	$T_J = 25^\circ\text{C}$, $I_F = 14\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$
Q_{RR} Reverse Recovery Charge	ALL	0.26	0.58	1.3	μC	
t_{on} Forward Turn-On Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

Thermal Resistance

$R_{\theta JC}$ Junction-to-Case	ALL	—	—	1.9	K/W ③	
$R_{\theta CS}$ Case-to-Sink	ALL	—	0.50	—	K/W ③	Mounting surface flat, smooth, and greased
$R_{\theta JA}$ Junction-to-Ambient	ALL	—	—	80	K/W ③	Typical socket mount

Typical SPICE Computer Model Parameters (For More Information See Application Note AN-975)

Device	Level, SPICE MOSFET Model	W (μm), Channel Width	L (μm), Channel Length	Theta (1/V), Mobility Modulation	UO ($\text{CM}^2/\text{V}\cdot\text{S}$), Surface Mobility	VTO (V), Threshold Voltage	R1 (Ω), Drain Resistance	R2 (Ω), Source Resistance	RG (Ω), Gate Resistance
All	3	0.532	1.2	0.12	450	3.47	0.055	0.02	1

CGSO (pf), Gate-Source Capacitance	CGD (fF), Gate-Drain Capacitance	E1 (V), Voltage Dependent Voltage Source	LD (nH), Drain Inductance	LS (nH), Source Inductance	LG (nH), Gate Inductance	IS (A), Diode Saturation Current	RS (Ω), Diode Bulk Resistance
730	C3	$4 + 0.95\text{VDG}$	4.5	7.5	7.5	1.4×10^{-13}	0.016

$C3 = 600\text{ pf} + 2.38 \times 10^{-20} (V_{GE})^{20} - 1.1 \times 10^{-21} (V_{GE})^{22}$

① Repetitive Rating; Pulse width limited by maximum junction temperature (see figure 5) Refer to current HEXFET reliability report

② @ $V_{DD} = 25\text{V}$, Starting $T_J = 25^\circ\text{C}$, $L = 530\text{ nH}$, $R_G = 25\Omega$, Peak $I_L = 14\text{A}$.

③ $I_{SD} \leq 14\text{A}$, $di/dt \leq 140\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, $T_J \leq 175^\circ\text{C}$, Suggested $R_G = 12\Omega$

④ $K/W = ^\circ\text{C}/\text{W}$, $W/K = \text{W}/^\circ\text{C}$

④ Pulse width $\leq 300\text{ }\mu\text{s}$; Duty Cycle $\leq 2\%$

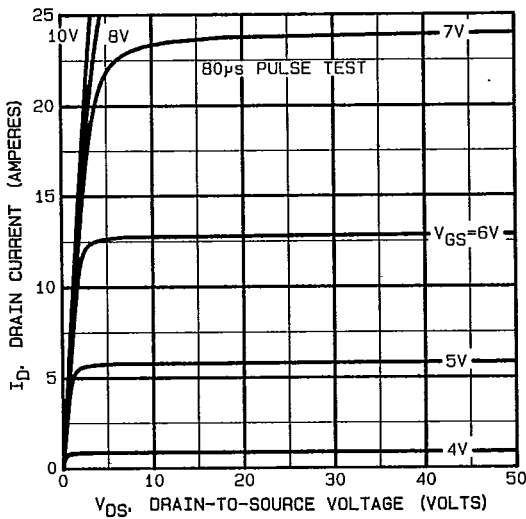


Fig. 1 — Typical Output Characteristics

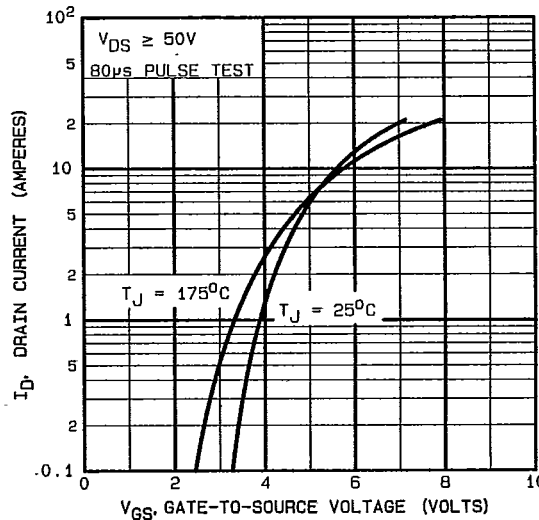


Fig. 2 — Typical Transfer Characteristics

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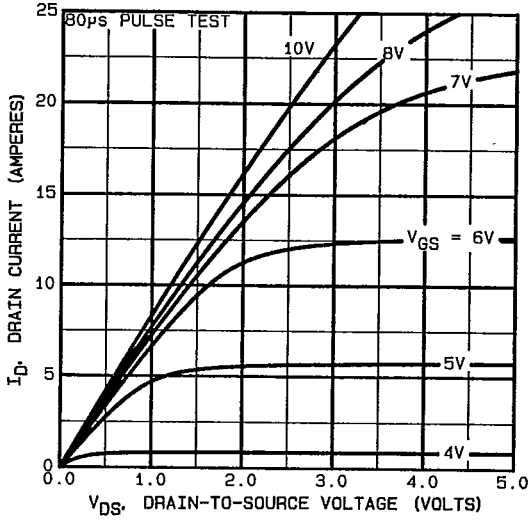


Fig. 3 — Typical Saturation Characteristics

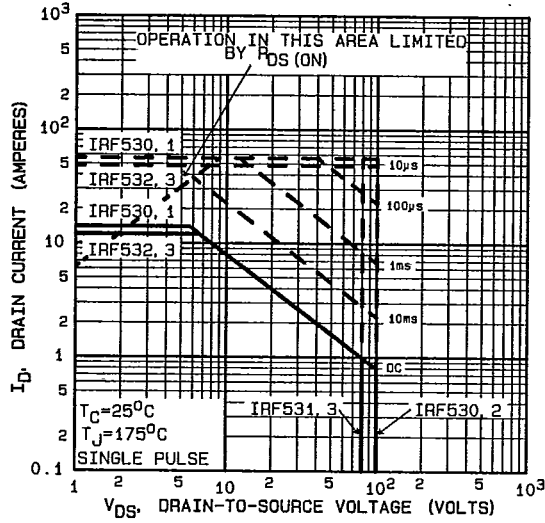


Fig. 4 — Maximum Safe Operating Area

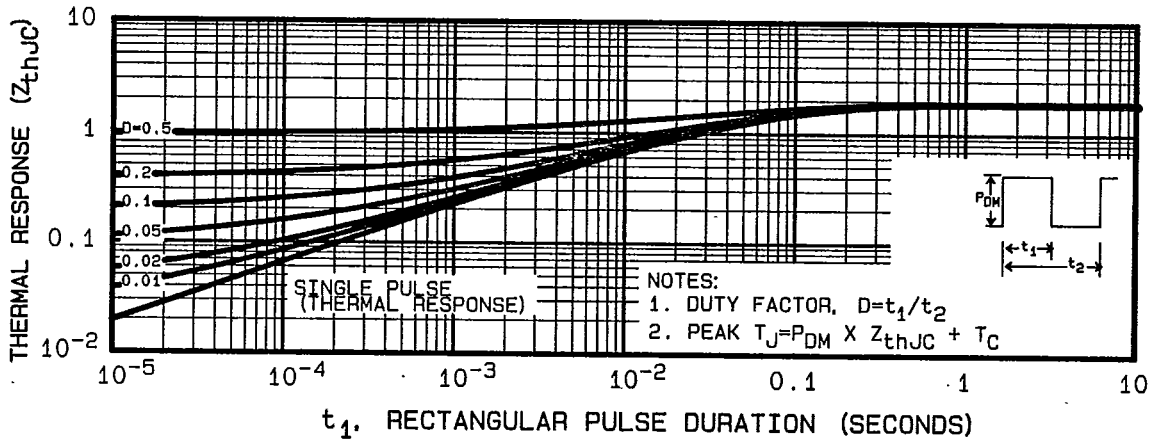


Fig. 5 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

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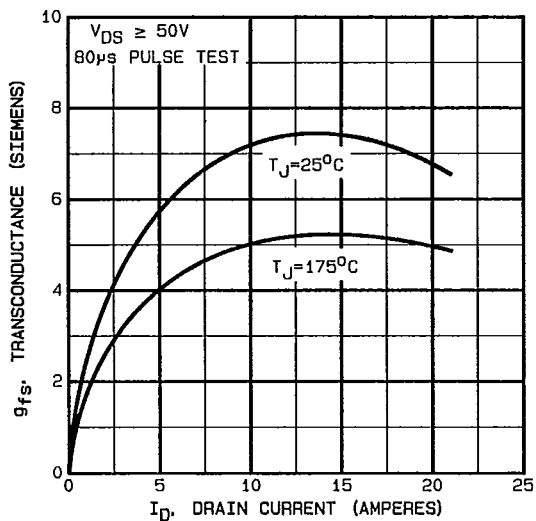


Fig. 6 — Typical Transconductance Vs. Drain Current

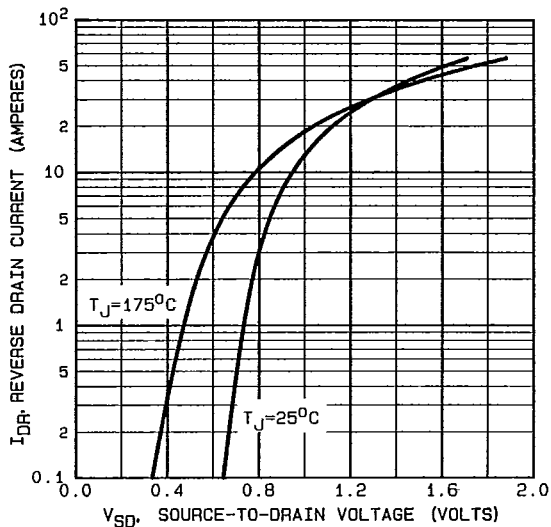


Fig. 7 — Typical Source-Drain Diode Forward Voltage

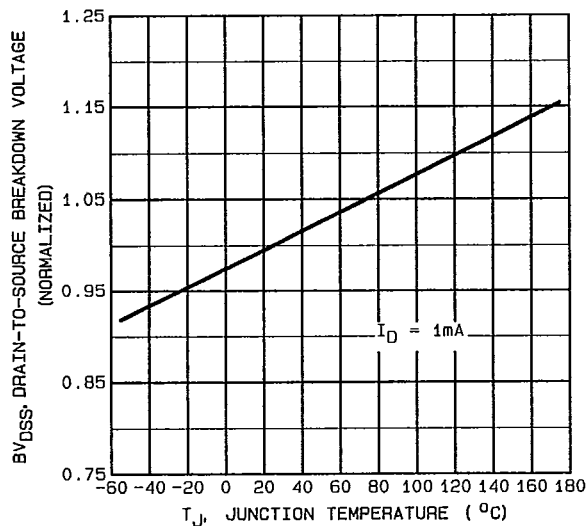


Fig. 8 — Breakdown Voltage Vs. Temperature

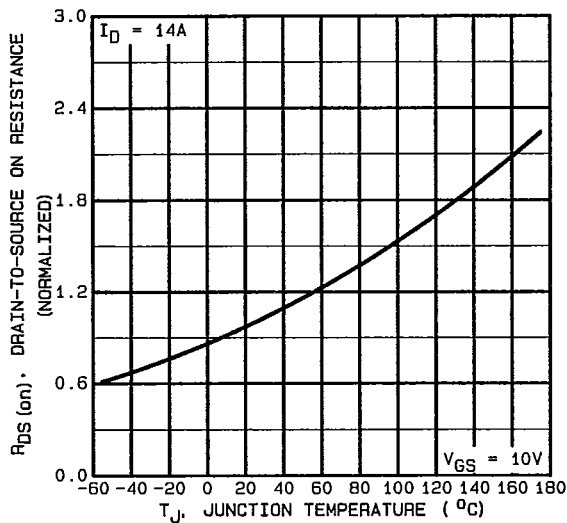


Fig. 9 — Normalized On-Resistance Vs. Temperature

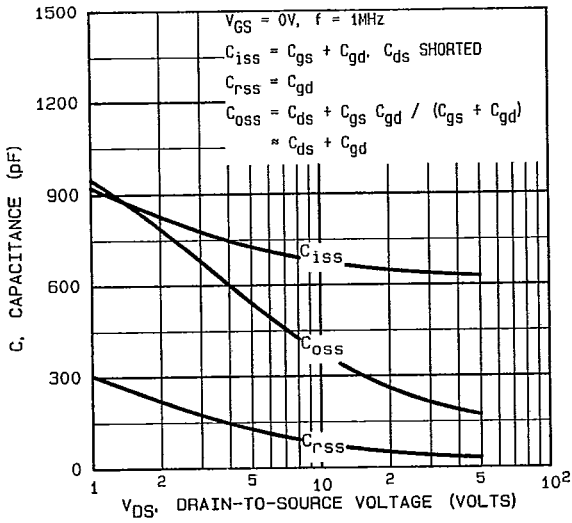


Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

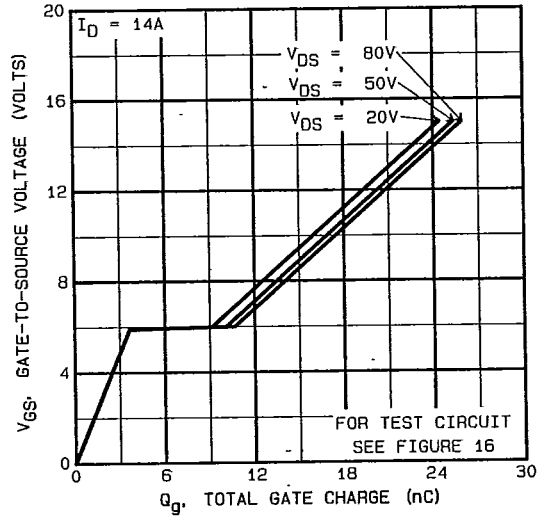


Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

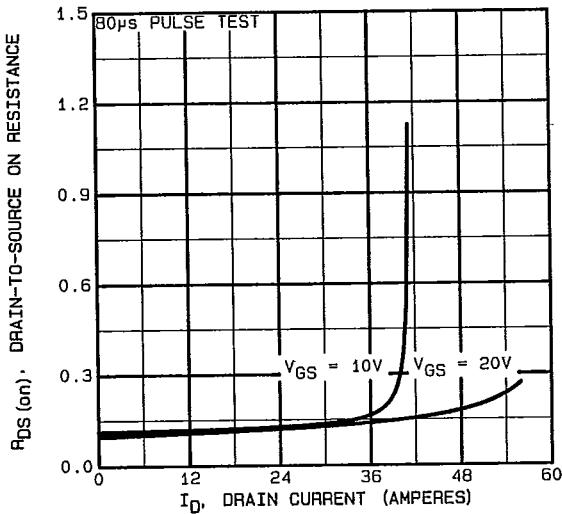


Fig. 12 — Typical On-Resistance Vs. Drain Current

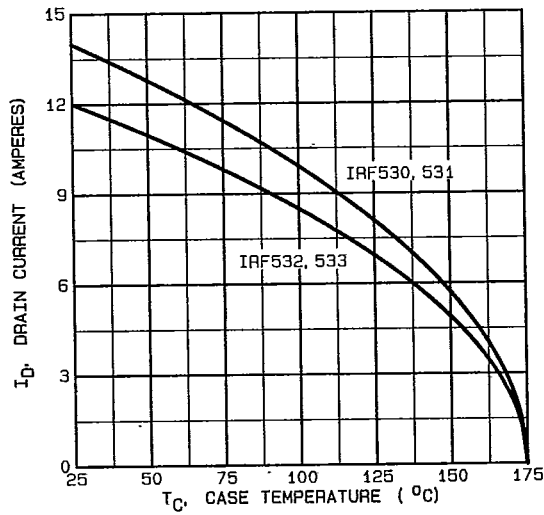


Fig. 13 — Maximum Drain Current Vs. Case Temperature

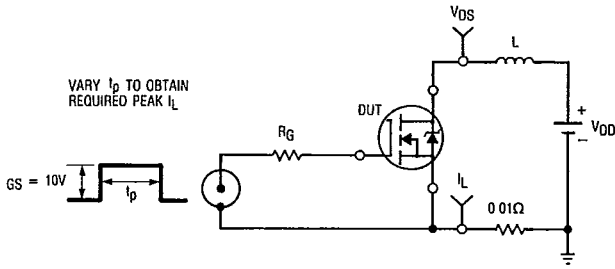


Fig. 14a — Unclamped Inductive Test Circuit

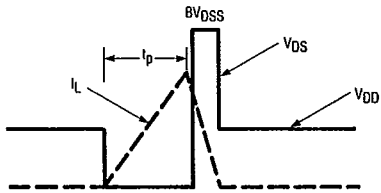


Fig. 14b — Unclamped Inductive Waveforms

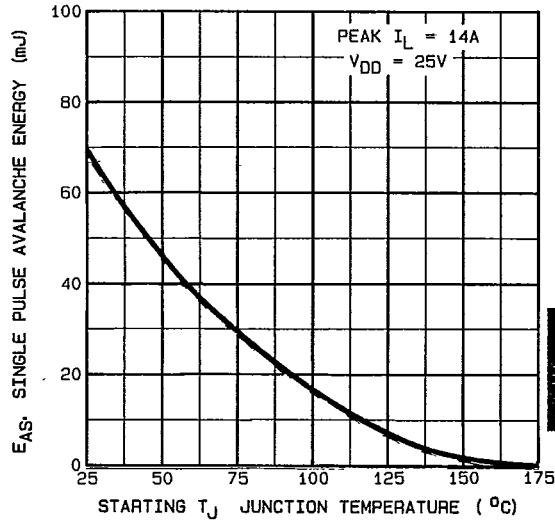


Fig. 14c — Maximum Avalanche Energy Vs. Starting Junction Temperature

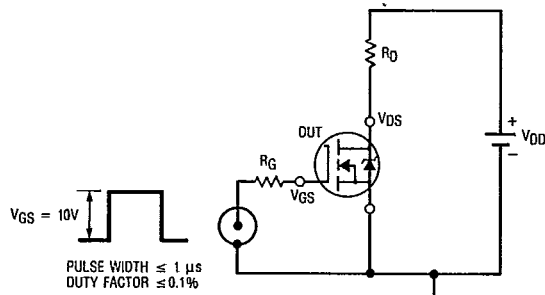


Fig. 15a — Switching Time Test Circuit

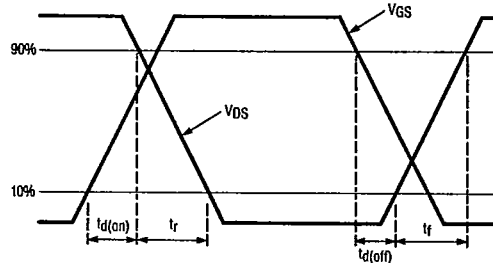


Fig. 15b — Switching Time Waveforms

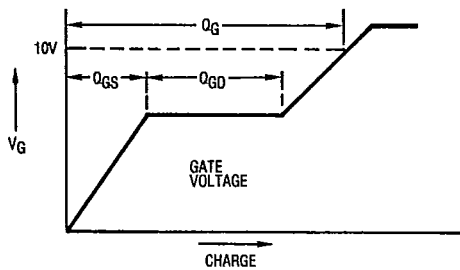


Fig. 16a — Basic Gate Charge Waveform

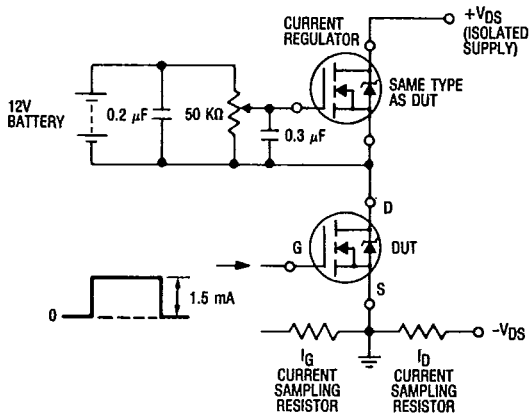


Fig. 16b — Gate Charge Test Circuit

IRF530, IRF531, IRF532, IRF533 Devices

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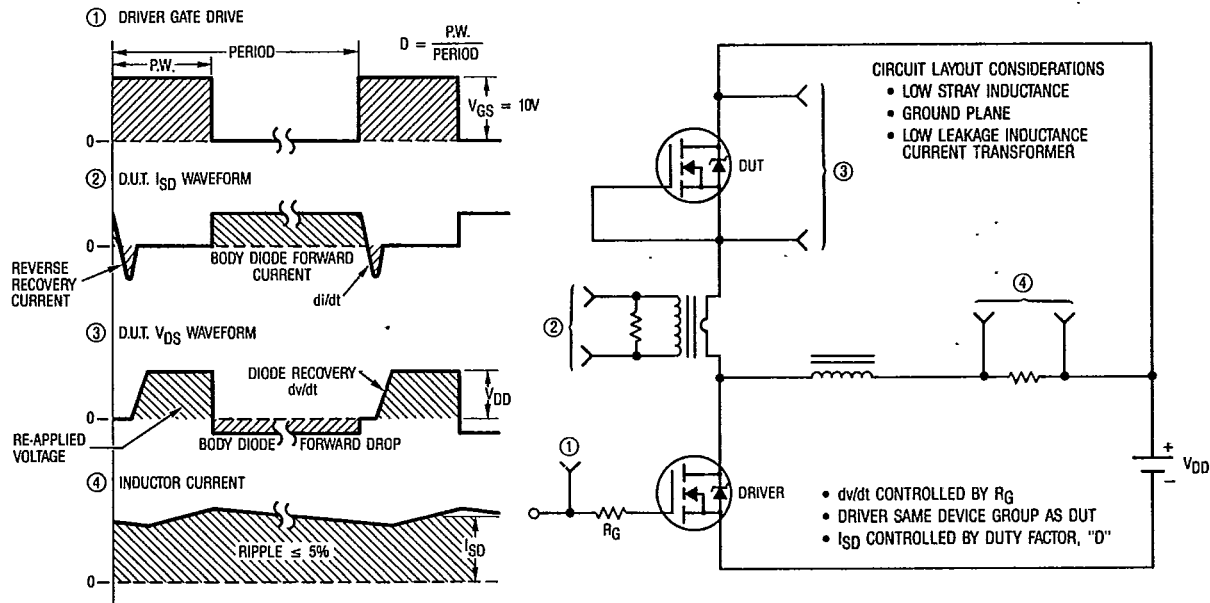
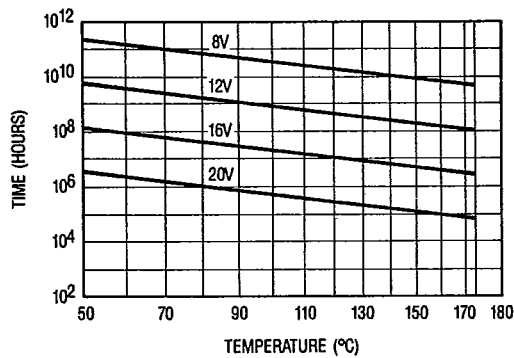
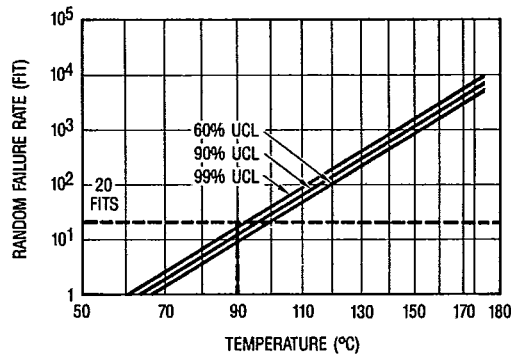


Fig. 17 — Peak Diode Recovery dv/dt Test Circuit



*Fig. 18 — Typical Time to Accumulated 1% Gate Failure



*Fig. 19 — Typical High Temperature Reverse Bias (HTRB) Failure Rate

*The data shown is correct as of January 15, 1987. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.